

[Please substitute claim 8 currently on file with the following amended claim:]

8. (Amended) The active matrix display device according to claim 1, wherein metal layers are formed on a drain region and a source region, respectively, of the first thin-film transistor and/or each of the second thin-film transistors, and portions of the respective metal layers are exposed through respective contact holes that are formed through a passivation film that covers the thin-film transistor.

[Please substitute claim 10 currently on file with the following amended claim:]

10. (Amended) The active matrix display device according to claim 1, wherein the active matrix device is liquid crystal device.

[Please add the following new claims:]

11. (Added) The active matrix display device according to claim 2, wherein the gate signal line is made of aluminum.
12. (Added) The active matrix display device according to claim 3, wherein the gate signal line is made of aluminum.
13. (Added) The active matrix display device according to claim 4, wherein the gate signal line is made of aluminum.
14. (Added) The active matrix display device according to claim 2, wherein a semiconductor layer of the first thin-film transistor and/or each of the second thin-film transistors is made of polysilicon.
15. (Added) The active matrix display device according to claim 3, wherein a semiconductor layer of the first thin-film transistor and/or each of the second thin-film transistors is made of polysilicon.

16. (Added) The active matrix display device according to claim 4, wherein a semiconductor layer of the first thin-film transistor and/or each of the second thin-film transistors is made of polysilicon.
17. (Added) The active matrix display device according to claim 2, wherein metal layers are formed on a drain region and a source region, respectively, of the first thin-film transistor and/or each of the second thin-film transistors, and portions of the respective metal layers are exposed through respective contact holes that are formed through a passivation film that covers the thin-film transistor.
18. (Added) The active matrix display device according to claim 3, wherein metal layers are formed on a drain region and a source region, respectively, of the first thin-film transistor and/or each of the second thin-film transistors, and portions of the respective metal layers are exposed through respective contact holes that are formed through a passivation film that covers the thin-film transistor.
19. (Added) The active matrix display device according to claim 4, wherein metal layers are formed on a drain region and a source region, respectively, of the first thin-film transistor and/or each of the second thin-film transistors, and portions of the respective metal layers are exposed through respective contact holes that are formed through a passivation film that covers the thin-film transistor.
20. (Added) The active matrix display device according to claim 17, wherein the metal layers are formed at the same time as a gate electrode of the thin-film transistor is formed.
21. (Added) The active matrix display device according to claim 18, wherein the metal layers are formed at the same time as a gate electrode of the thin-film transistor is formed.

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22. (Added) The active matrix display device according to claim 19, wherein the metal layers are formed at the same time as a gate electrode of the thin-film transistor is formed.
23. (Added) The active matrix display device according to claim 2, wherein the active matrix device is liquid crystal device.
24. (Added) The active matrix display device according to claim 3, wherein the active matrix device is liquid crystal device.
25. (Added) The active matrix display device according to claim 4, wherein the active matrix device is liquid crystal device.
26. (Added) The active matrix display device according to claim 5, wherein the active matrix device is liquid crystal device.

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